Charge-trapping characteristics of fluorinated thin ZrO₂ film for nonvolatile memory applications

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The effects of fluorine treatment on the charge-trapping characteristics of thin ZrO₂ film are investigated by physical and electrical characterization techniques. The formation of silicate interlayer at the ZrO₂/SiO₂ interface is effectively suppressed by fluorine passivation. However, excessive fluorine diffusion into the Si substrate deteriorates the quality of the SiO₂/Si interface. Compared with the ZrO₂-based memory devices with no or excessive fluorine treatment, the one with suitable fluorine-treatment time shows higher operating speed and better retention due to less resistance of built-in electric field (formed by trapped electrons) against electron injection from the substrate and smaller trap-assisted tunneling leakage, resulting from improved ZrO₂/SiO₂ and SiO₂/Si interfaces. © 2014 AIP Publishing LLC. [http://dx.doi.org/10.1063/1.4873388]

Metal-oxide-nitride-oxide-silicon (MONOS)-type nonvolatile memory with discrete traps in the dielectric for charge storage is considered as a promising candidate to replace its floating-gate counterpart due to stronger scaling ability and higher reliability. Recently, high-k dielectrics have been proposed instead of conventional Si₃N₄ as charge-trapping layer (CTL) to achieve lower operating voltage and higher charge-trapping efficiency. Among various high-k dielectrics, Hf-based oxides (e.g., HfO₂ and HfON) have been extensively investigated as CTL mainly because of its large conduction-band offset relative to SiO₂. The physical properties of the films with and without fluorination and found that MONOS device with nitrided ZrO₂ showed better performance than that without nitridation due to nitrogen passivation of the ZrO₂ film. Besides nitrogen, fluorine is also an excellent passivant to remove oxide defects and strengthen the dielectric films due to its very high electronegativity. Therefore, fluorination is an effective way to improve the charge-trapping characteristics of dielectrics. In this work, based on MONOS capacitors, the charge-trapping characteristics of ZrO₂ with and without fluorination incorporation are studied. Detailed analysis of fluorine treatment on the device performance is also carried out.

MONOS capacitors with Al/Al₂O₃/ZrO₂/SiO₂/Si were fabricated on p-type (100) substrate. After the standard RCA cleaning, 2-nm SiO₂ tunneling oxide was grown on the wafers by thermal dry oxidation. Then 3-nm ZrO₂ was deposited on the SiO₂ by sputtering using a Zr target in an Ar/O₂ (8/1) mixed ambient. Following that, some samples were treated by a CHF₃ + O₂ (10 SCCM/1 SCCM) plasma at 20 W for 150 s and 400 s, respectively. The low-concentration O₂ was used to remove the carbon and hydrogen in the plasma.

Then, 15-nm Al₂O₃ was deposited by atomic layer deposition using trimethyl-aluminum (Al(CH₃)₃) and H₂O as precursors at 300 °C. Following that, all the samples went through a post-deposition annealing in N₂ at 900 °C for 30 s. Finally, Al was evaporated and patterned as gate electrodes followed by a forming-gas annealing at 300 °C for 20 min. The sample without fluorine treatment was denoted as ZrO, while the samples with 150-s and 400-s fluorine treatment were denoted as LF-ZrO and HF-ZrO, respectively. In addition, Al/Al₂O₃/SiO₂/Si (denoted as MAOS) and Al/ZrO₂/SiO₂/Si (denoted as MNOS) capacitors were also fabricated by the same process to study the charge-trapping characteristics of the ZrO₂ film. The physical properties of the films with and without fluorine treatment were analyzed by transmission electron microscopy (TEM), secondary ion mass spectroscopy (SIMS), and X-ray photoelectron spectroscopy (XPS). The electrical characteristics of the devices were measured by HP4284A LCR meter and HP4156A semiconductor parameter analyzer.

Fig. 1 shows the cross-sectional TEM image of the MONOS capacitors with and without the fluorine treatment, where the physical thickness remains the same after the fluorine treatment, indicating negligible etching of the ZrO₂ film due to the low energy of the fluorine plasma treatment. Fig. 2(a) displays the SIMS depth profile of the samples with various fluorine-treatment times to evaluate the fluorine distribution. It is clear that fluorine is mainly located in the ZrO₂/SiO₂ stack and decreases rapidly in the Si substrate, indicating strong fluorine passivation in the ZrO₂/SiO₂ stack. Also, the fluorine atoms diffuse more into the Si substrate for longer fluorine-treatment time. This is consistent with the XPS data in Fig. 2(b), where the Si 2p spectrum from the substrate for the HF-ZrO sample shifts to higher binding energy by 0.05 eV relative to those for the ZrO and LF-ZrO samples, implying the formation of Si-F bonds. Fig. 2(c) shows the Zr 3d spectrum combined with curve-fitting lines. For the ZrO sample, the Sr 3d spectrum displays distinct doublet at 184.7 eV (Zr 3d₃/₂) and 182.3 eV (Zr 3d₅/₂), agreeing with Zr–O bonding in the ZrO₂ film. After the fluorine treatment,
the spectrum shifts to higher binding energy by 0.5 eV, indicating that F is bonded with Zr. Moreover, the Zr spectrum can be decomposed into two components, corresponding to ZrO$_2$ (182.3 eV for Zr 3$d_{5/2}$) and Zr silicate formed by the ZrO$_2$/SiO$_2$ interfacial reaction (182.7 eV for Zr 3$d_{5/2}$). Compared with the ZrO sample, the much smaller area of the silicate component for the LF-ZrO and HF-ZrO samples indicates negligible formation of the Zr silicate interlayer due to sufficient fluorine passivation. The formation of the interlayer consumes the SiO$_2$ tunneling oxide, and also it has smaller bandgap ($\sim$6.6 eV) and more defects than thermally grown SiO$_2$ ($\sim$8.9 eV). Therefore, an abrupt interface without interlayer is desirable for good data retention.

Fig. 3(a) displays the C-V loops under ±8 MV/cm sweeping for the MAOS and MNOS samples. The trapped-charge density ($Q_{ox}$) in the device can be calculated by the expression below

$$Q_{ox} \approx \frac{\Delta V_{FB} C_{ox}}{q},$$  \hspace{1cm} (1)

where $\Delta V_{FB}$ is the memory window from the C-V loops, $C_{ox}$ is the capacitance density of the samples, and q is the electron charge. The $Q_{ox}$ for the MAOS and MNOS samples is about $3.5 \times 10^{10}$ cm$^{-2}$ and $1.1 \times 10^{12}$ cm$^{-2}$, respectively. The much higher $Q_{ox}$ for the MNOS sample than that for the MAOS one at the same operating condition indicates that the charge-trapping site is mainly in the ZrO$_2$ layer. In addition, compared with the MAOS sample with counterclockwise hysteresis loop, the MNOS one exhibits a clockwise hysteresis loop, suggesting that charges inject from the Al electrode into the ZrO$_2$ layer at the forward sweeping (from $-8$ MV/cm to $+8$ MV/cm) mainly due to the smaller barrier height at the Al/ZrO$_2$ interface ($\Delta E_C \sim 1.6$ eV for Al/ZrO$_2$; $\sim3.0$ eV for Al/Al$_2$O$_3$). Fig. 3(b) depicts the 1-MHz C-V hysteresis loops of the MONOS devices, where the memory window for the ZrO, LF-ZrO, and HF-ZrO samples is 4.8 V, 3.8 V, and 5.1 V, respectively. The smaller window for the LF-ZrO sample than the ZrO sample is due to the suppressed formation of interlayer by fluorine passivation, while the largest window for the HF-ZrO sample suggests extra traps generated by excessive fluorine treatment. The C-V curve of the HF-ZrO sample shows more severe stretch-out characteristic than the ZrO and LF-ZrO samples, implying its higher interface-state density ($D_{it}$) at the SiO$_2$/Si interface. Using the Terman’s method, the HF-ZrO sample has an extracted $D_{it}$ of $7.4 \times 10^{12}$ cm$^{-2}$, corresponding to 8.8% and 17.5% higher than the ZrO sample ($6.8 \times 10^{12}$ cm$^{-2}$) and the LF-ZrO sample ($6.3 \times 10^{12}$ cm$^{-2}$), respectively. Appropriate fluorine incorporation can passivate the SiO$_2$/Si interface,
leading to the smallest $D_t$ for the LF-ZrO sample. However, owing to the high electronegativity of fluorine, excessive fluorine can distort and even cleave the Si-Si bonds at the interface to form dangling Si bonds and Si-F bonds (as demonstrated in Fig. 2), resulting in the highest $D_{it}$ and thus the largest window for the HF-ZrO sample.

Fig. 4(a) displays the gate leakage ($J_G$) of the MONOS devices as a function of electric field across SiO$_2$ ($E_{OX}$) by applying positive gate voltage ($V_G$), corresponding to electron injection from the substrate. The LF-ZrO sample has a smaller leakage at low $E_{OX}$ than the ZrO and HF-ZrO samples due to fewer traps at/near its interface and thus reduced trap-assisted tunneling. Moreover, the $J_G$-$E_{OX}$ curve of the HF-ZrO sample presents an obvious notch (denoted as A), where $J_G$ decreases with $E_{OX}$ and then increases again. This is associated with its high $D_{it}$ at the SiO$_2$/Si interface. Due to Coulomb repulsion, electrons trapped by interface states can form a built-in electric field ($E_{in}$) opposite to the external electric field $E_{OX}$ induced by $V_G$, which is approximately given by

$$E_{in} \approx \frac{1}{4\pi\varepsilon R^2} Q_i,$$  \hspace{1cm} (2)

where $Q_i$ is the trapped charge; $\varepsilon$ is the permittivity of the dielectric that $E_{in}$ passes through; and $R$ represents the distance between the trapped-charge centroid and the substrate. $E_{in}$ tends to block the electron injection and also electrons filled in the shallow traps near the interface would flow back into the substrate due to $E_{in}$, both of which can offset the electron injection from the substrate. With increasing $E_{OX}$ and establishing a balance between electron trapping and de-trapping, $J_G$ increases with $E_{OX}$ again. A similar notch (denoted as B) is also observed for the ZrO sample due to high trap density at the ZrO$_2$/SiO$_2$ interlayer and high $D_{it}$ at the SiO$_2$/Si interface. On the contrary, no notch in the $J_G$-$E_{OX}$ curve for the LF-ZrO sample suggests that its $E_{in}$ is weak and has little effect on electron injection, resulting from the suppressed formation of interlayer at the ZrO$_2$/SiO$_2$ interface by the fluorine passivation as well as low $D_{it}$ at the SiO$_2$/Si interface by avoiding excessive fluorine diffusion to the Si substrate. For the ZrO and HF-ZrO samples, the traps generated by the Zr-silicate interlayer and high interface states lead to larger $V_{FB}$ shift (thus larger $Q_i$) at low electric field as shown in Fig. 4(b). Moreover, these trapped charges at the ZrO$_2$/SiO$_2$ and SiO$_2$/Si interfaces make the trapped-charge centroid closer to the substrate compared with those located in the ZrO$_2$ film, thus resulting in stronger $E_{in}$ against electron injection according to Eq. (2). This is consistent with the phenomenon that the $J_G$ of the LF-ZrO...
sample increases more rapidly with $E_{OX}$ than those of the ZrO and HF-ZrO samples, which becomes more obvious as the Fowler-Nordheim (FN) tunneling current dominates $I_G$ (FN current is exponentially proportional to electric field of $E_{OX}$).\textsuperscript{19} It should be noted that the little impact of $E_{OX}$ on electron injection from the substrate is beneficial to supplying sufficient electrons for the memory device, thus contributing to the larger $V_{FB}$ shift ($\sim$3.1 V versus 2.8 V for ZrO, 2.5 V for HF-ZrO) at high electric field for the LF-ZrO sample in Fig. 4(b). On the other hand, small leakage at low electric field normally indicates suppressed trap-assisted tunneling under retention mode and thus is beneficial for data retention. Therefore, the steeper $I_G$-$E_{OX}$ characteristic of the LF-ZrO sample is desirable for memory device to achieve high operating speed as well as good data retention.

Fig. 5(a) displays the retention characteristics of the MONOS capacitors, and the retention data for the ZrO sample with thicker SiO$_2$ tunneling layer (SiO$_2$ $\sim$ 3.5 nm) are also measured to study charge-loss paths under the retention mode. The ZrO sample with thicker SiO$_2$ shows excellent data retention with no charge loss even after $10^4$ s (Fig. 4(b)). On the other hand, small leakage at low electric field normally indicates suppressed trap-assisted tunneling under retention mode and thus is beneficial for data retention. Therefore, the steeper $I_G$-$E_{OX}$ characteristic of the LF-ZrO sample is desirable for memory device to achieve high operating speed as well as good data retention.

In summary, the effects of fluorine treatment on the charge-trapping characteristics of thin ZrO$_2$ film are investigated. Compared with the memory devices with no or excessive fluorine treatment, the one with suitable fluorine treatment time shows better characteristics due to suppressed interlayer growth by fluorine passivation of the ZrO$_2$/SiO$_2$ interface and also fewer interface states by avoiding excessive fluorine diffusion to the substrate. Therefore, ZrO$_2$ film with appropriate fluorine incorporation is a promising candidate as CTL for high-performance nonvolatile memory applications.

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